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- oxide **91** (1988) 57; **94** (1989) 895; **95** (1989) 505; **96** (1989) 363, 785; **99** (1990) 399, 905
- phosphide **99** (1990) 625; **100** (1990) 1
- selenide **91** (1988) 57, 617, 639; **92** (1988) 196; **93** (1988) 259, 656, 673, 679, 692, 697, 703, 714; **94** (1989) 1, 69, 441; **95** (1989) 512, 522, 529, 533, 538, 567, 572, 580, 589; **96** (1989) 217, 513, 756; **98** (1989) 302, 857; **99** (1990) 403, 408, 413, 418, 427; **100** (1990) 281
- selenide telluride **98** (1989) 37
- sulphide **91** (1988) 57, 111; **92** (1988) 128; **93** (1988) 259, 686, 714; **94** (1989) 441, 983; **95** (1989) 505, 572; **96** (1989) 979; **99** (1990) 451, 464; **100** (1990) 405
- sulphoselenide **93** (1988) 662, 708; **94** (1989) 102; **95** (1989) 525; **99** (1990) 422, 446
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